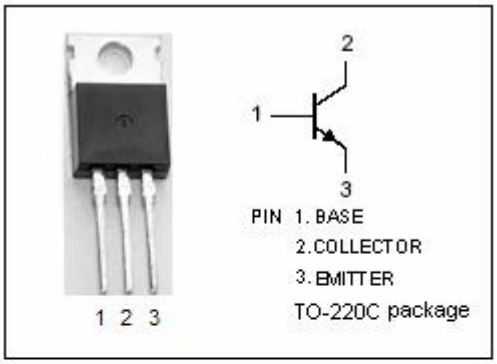
isc Silicon NPN Power Transistors — BUV26G

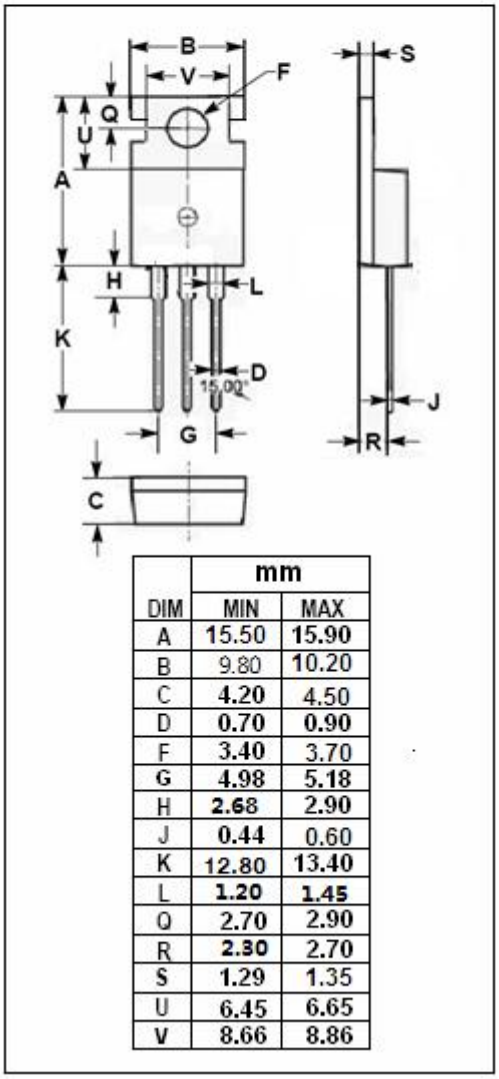
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 90V(Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for fast switching applications such as high frequency and efficiency converters, switching regulators and motor control.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	90	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	14	A
I_{CM}	Collector Current-Peak	25	A
I_B	Base Current-Continuous	4	A
I_{BM}	Base Current-Peak	6	A
P_C	Collector Power Dissipation @ T_C=25℃	65	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.92	℃/W

isc Silicon NPN Power Transistors BUV26G

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA ;I_B= 0	90			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 12A; I_B= 1.2A			1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 0.6A			0.6	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 12A; I_B= 1.2A			2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 0.6A			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}=180V; I_E=0			1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0			1.0	mA